

Shifan Gao

List of Publications by Year in descending order

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Version: 2024-02-01

11
papers

73
citations

2258059

3
h-index

2272923

4
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all docs

11
docs citations

11
times ranked

82
citing authors

#	ARTICLE	IF	CITATIONS
1	Rapid and Quantitative Analysis of Exosomes by a Chemiluminescence Immunoassay Using Superparamagnetic Iron Oxide Particles. <i>Journal of Biomedical Nanotechnology</i> , 2019, 15, 1792-1800.	1.1	23
2	Programmable Linear RAM: A New Flash Memory-based Memristor for Artificial Synapses and Its Application to Speech Recognition System. , 2019, , .		11
3	MRAM Acceleration Core for Vector Matrix Multiplication and XNOR-Binarized Neural Network Inference. , 2020, , .		9
4	Improvement of Ferroelectricity and Reliability in $\text{Hf}_{0.5}\text{Zr}_{0.5}\text{O}_2$ Thin Films With Two-Step Oxygen Vacancy Engineering. <i>IEEE Electron Device Letters</i> , 2022, 43, 1057-1060.	3.9	8
5	An Euler-Lagrange Equation Oriented Solution for Write Energy Minimization of STT-MRAM. <i>IEEE Transactions on Electron Devices</i> , 2019, 66, 3686-3689.	3.0	5
6	Neural Network Acceleration and Voice Recognition with a Flash-based In-Memory Computing SoC. , 2021, , .		5
7	A Compute-in-Memory Architecture Compatible with 3D NAND Flash that Parallely Activates Multi-Layers. , 2021, , .		4
8	Probing Write Error Rate and Random Telegraph Noise of MgO Based Magnetic Tunnel Junction Using a High Throughput Characterization System. , 2019, , .		3
9	Superior Data Retention of Programmable Linear RAM (PLRAM) for Compute-in-Memory Application. , 2020, , .		3
10	Systematic Study of Medium States in Spin-Transfer Torque Magnetoresistance Random Access Memory and Their Implication for the Bit Error Rate. <i>IEEE Electron Device Letters</i> , 2020, 41, 557-560.	3.9	2
11	High-efficiency array-level MRAM parameters extraction with the device-in-series test structure. <i>Journal of Applied Physics</i> , 2022, 131, .	2.5	0